

Silicon NPN Power Transistors

2SC2943

DESCRIPTION

- With TO-3PN package
- High reliability
- Low saturation voltage

APPLICATIONS

- Color & B/W TV power supply
- Active power filter
- Industrial use power supply
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

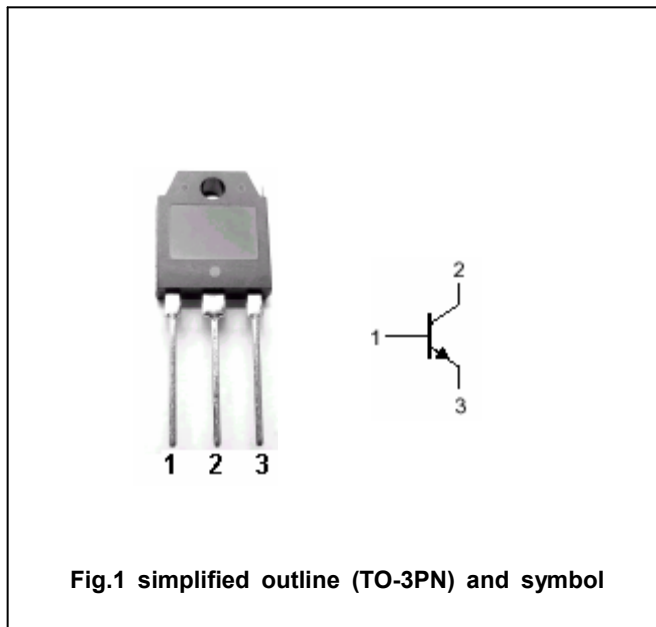


Fig.1 simplified outline (TO-3PN) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	390	V
V _{CEO}	Collector-emitter voltage	Open base	250	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		15	A
I _B	Base current (DC)		5	A
P _C	Collector power dissipation	T _C =25°C	80	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	250			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =0.1mA ; I _C =0	7			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =0.1mA ; I _E =0	390			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =6A ; I _B =1.2A			0.8	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =6A ; I _B =1.2A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =350V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =5V	20			
f _T	Transition frequency	I _C =1A ; V _{CE} =10V		20		MHz

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PACKAGE OUTLINE

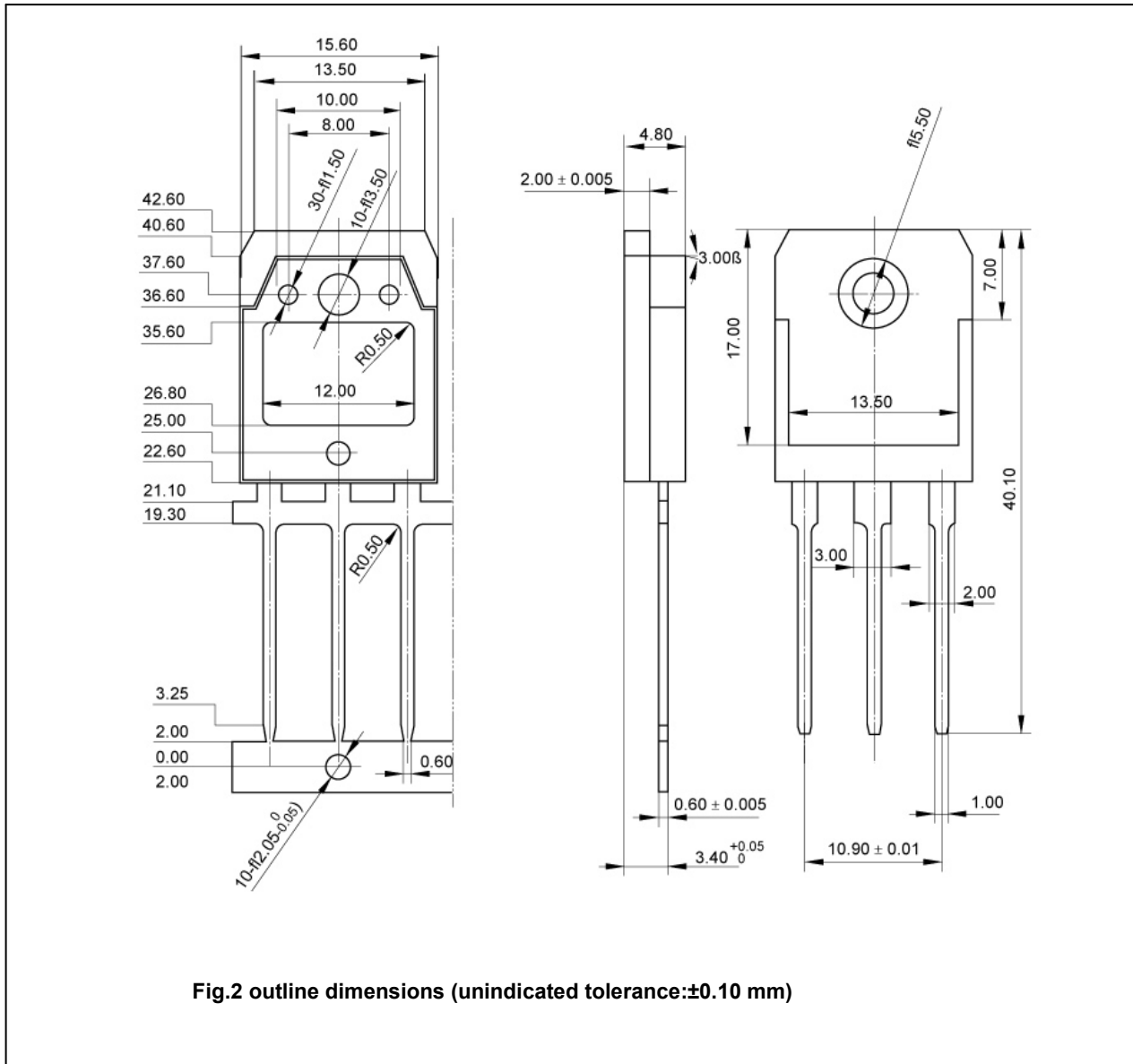


Fig.2 outline dimensions (unindicated tolerance:±0.10 mm)